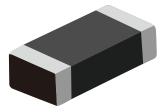


# FEATURES

Fast response, instantly clamping the transient over voltage.

- High surge current handling capability.
- High energy absorption capability.
- Low clamping voltages, providing better surge protection.
- Low capacitance values, providing digital switching circuitryprotection.
- High insulation resistance, preventing electric arcing to the adjacent

devices or circuits.



# **APPROVALS**

RoHSCompliance with 2011/65/EUHFCompliance with IEC61249-2-21:2003

# **APPLICATIONS**

Universal Serial Bus (USB).	
Mobile communication.	
Computer/DSP product.	
Video and audio ports.	
Portable/Hand-Held Products.	
Data, Diagnostic I/O ports.	

# **ELECTRICAL SPECIFICATION**

Test condition		
Varistor voltage	In = 1 mA DC	
Leakage current	Vdc = 36 V DC	
Maximum clamping voltage	Ic = 1 A	
Rated peak single pulse transient current	8 / 20 μs waveform, +/- each 1 time induce	
Capacitance	10/1000 μs waveform	
Insulation resistance after reflow soldering	f = 1MHz, Vrms = 0.5 V	



# **ELECTRICAL SPECIFICATION**

Electrical specification				
Maximum allowable continuous DC voltage	36	V		
trigger voltage / Varistor voltage / breakdown voltage	125	V		
Maximum clamping voltage	220	V	Maximum	
Rated peak single pulse transient current	1	А	Maximum	
Nonlinearity coefficient	> 12			
Leakage current at continuous DC voltage	< 0.1	μA		
Response time	< 0.5	ns		
Varistor voltage temperature coefficient	< 0.05	%/°C		
Capacitance measured at 1MHz	5	pF	Typical	
Capacitance tolerance	-50 to +50	%		
Insulation resistance after reflow soldering on PCB	> 10	MΩ		
Operating ambient temperature	-55 to +125	°C		
Storage temperature	-55 to +125	°C		



### **RELIABILITY TESTING PROCEDURES**

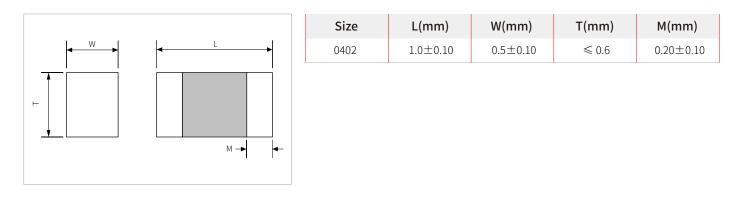
Reliability parameter		Test methods and remarks	Test requirement	
Pulse current capability	lmax 8/20 μs	IEC 1051-1, Test 4.5. 10 pulses in the same direction at 2 pulses per minute at maximum peak current	d Vn /Vn≤10% no visible damage	
Electrostatic discharge capability	ESD C=150 pF, R=330Ω	IEC 1000-4-2 Each 10 times in positive/negative direction in 10 sec at 8KV contact discharge (Level 4)	d Vn /Vn≤10% no visible damage	
	Thermal shock	IEC 68-2-14 Condition for 1 cycle Step 1 : Min. –40°C, 30±3 min. Step 2 : Max. +125°C, 30±3 min. Number of cycles: 30 times	d Vn /Vn≤5% no visible damage	
Environmenta l reliability	Low temperature	IEC 68-2-1 Place the chip at -40 $\pm$ 5°C for 1000 $\pm$ 12hrs. Remove and place for 24 $\pm$ 2hrs at room temp. condition, then measure	d Vn /Vn≤5% no visible damage	
	High temperature	IEC 68-2-2 Place the chip at $125\pm5^{\circ}$ C for $1000\pm24$ hrs. Remove and place for $24\pm2$ hrs at room temp. condition, then measure	d Vn /Vn≤5% no visible damage	
	Heat resistance	IEC 68-2-3 Apply the rated voltage for 1000±48hrs at 85±3°C. Remove and place for 24±2hrs at room temp. condition, then measure	d Vn /Vn≤5% no visible damage	
	Humidity resistance	IEC 68-2-30 Place the chip at 40±2°C and 90 to 95% humidity for 1000±24hrs. Remove and place for 24±2hrs at room temp. condition, then measure	d Vn /Vn≤10% no visible damage	
	Pressure cooker test	Place the chip at 2 atm, 120°C, 85%RH for 60 hrs. Remove and place for 24 $\pm$ 2hrs at room temp. condition, then measure	d Vn /Vn≤10% no visible damage	
	Operating life	Apply the rated voltage for 1000±48hrs at 125±3°C. Remove and place for 24±2hrs at room temp. condition, then measure	d Vn /Vn≤10% no visible damage	
Mechanical Reliability	Adhesive strength	IEC 68-2-22 Applied force on SMD chip by fracture from PCB	Strength>10 N no visible damage	



## MATERIAL SPECIFICATION

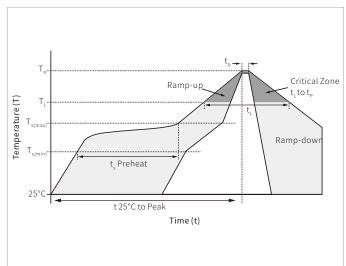
Body	Internal electrode	External electrode	Thickness of Ni/Sn plating layer
ZnO based ceramics	Silver – Palladium	Silver – Nickel – Tin	Nickel $> 1\mu$ m, Tin $> 2\mu$ m

### **DIMENSION SPECIFICATION**



### **SOLDERING RECOMMENDATIONS**

Reflow Condition		Lead-free assembly
Pre Heat	Temperature Max $(T_{s(min)})$	150°C
	Temperature Max (T <sub>s(max)</sub> )	200°C
	Time (min to max) (t <sub>s</sub> )	60 – 180 secs
Average ramp up rate (Liquidus Temp (T <sub>L</sub> ) to peak		3°C/second max
T <sub>s(max)</sub> to T <sub>L</sub> - Ramp-up Rate		3°C/second max
Reflow	Temperature (T <sub>L</sub> ) (Liquidus)	217°C
	Time (min to max) $(t_{L})$	60 – 150 seconds
Peak Temperature (T,)		260°C
Time within 5°C of actual peak Temperature ( $t_p$ )		20 – 40 seconds
Ramp-down Rate		6°C/second max
Time 25°C to peak Temperature (T <sub>P</sub> )		8 minutes max.
Do not exceed		260°C





### **DRDERING INF ORMATIOON**

Part Number	Package&Size	QTY/Reel	Reel Size	
SME0402B36MA	0402 (1.0 x 0.5 mm)	10000PCS	7"	



### Headquarters

No.3387 Shendu Road Pujiang I&E Park Minhang Shanghai China 201000

#### Hotline 400-021-5756

400-021-0700

Web Https://www.semiware.com Tel: 86-21-3463-7458 Email: sales18@semiware.com

### **Customer Service**

Tel: 86-21-5484-1001 Email: sales17@semiware.com

#### **Technical Support**

Tel: 86-21-3463-7654 Email: fae01@semiware.com

### **Complaint & Suggestions**

Tel: 86-21-3463-7172 Ext: 8868 Email: cs03@semiware.com

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